











CSD18540Q5B

SLPS488B -JUNE 2014-REVISED APRIL 2017

# CSD18540Q5B 60-V, N-Channel NexFET™ Power MOSFETs

#### **Features**

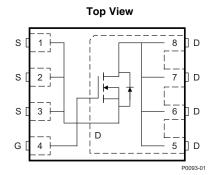
- Ultra-Low Qa and Qad
- Low-Thermal Resistance
- Avalanche Rated
- Lead-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

## Applications

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Isolated Converter Primary Side Switch
- Motor Control

## 3 Description

This 1.8-m $\Omega$ , 60-V NexFET<sup>TM</sup> power MOSFET is designed to minimize losses in power conversion applications with a SON 5-mm × 6-mm package.



## R<sub>DS(on)</sub> vs V<sub>GS</sub> $T_C = 25$ °C, $I_D = 28$ A R<sub>DS(on)</sub> - On-State Resistance (mΩ) $T_C = 125$ °C, $I_D = 28$ A 3.5 2.5 2 1.5 0.5 6 8 10 12 14 V<sub>GS</sub> - Gate-to-Source Voltage (V) D007

### **Product Summary**

$T_A = 25^\circ$	С	TYPICAL VA	UNIT				
$V_{DS}$	Drain-to-Source Voltage	60					
$Q_g$	Gate Charge Total (10 V) 41						
$Q_{gd}$	Gate Charge Gate-to-Drain 6.7						
D	Drain-to-Source On Resistance	V <sub>GS</sub> = 4.5 V 2.6		mΩ			
R <sub>DS(on)</sub>	Diam-to-Source Off Resistance	V <sub>GS</sub> = 10 V 1.8		11122			
$V_{GS(th)}$	Threshold Voltage 1.9						

## Device Information<sup>(1)</sup>

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18540Q5B	2500	13-Inch Reel	SON	Tape
CSD18540Q5BT	250	7-Inch Reel	5.00-mm × 6.00-mm Plastic Package	and Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Absolute Maximum Ratings**

T <sub>A</sub> = 2	5°C	VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	60	V
$V_{GS}$	Gate-to-Source Voltage	±20	V
	Continuous Drain Current (Package Limited)	100	
$I_D$	Continuous Drain Current (Silicon Limited), $T_C = 25^{\circ}C$	205	Α
	Continuous Drain Current <sup>(1)</sup>	29	
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	400	Α
n	Power Dissipation <sup>(1)</sup>	3.8	W
P <sub>D</sub>	Power Dissipation, T <sub>C</sub> = 25°C	188	VV
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction, Storage Temperature	-55 to 175	°C
E <sub>AS</sub>	Avalanche Energy, Single Pulse $I_D$ = 80 A, L = 0.1 mH, $R_G$ = 25 $\Omega$	320	mJ

- (1) Typical  $R_{\theta JA} = 40^{\circ}\text{C/W}$  on a 1-in<sup>2</sup>, 2-oz Cu pad on a 0.06-in thick FR4 PCB.
- (2) Max  $R_{\theta,IC} = 0.8^{\circ}C/W$ , pulse duration  $\leq 100 \mu s$ , duty cycle  $\leq$

#### **Gate Charge**

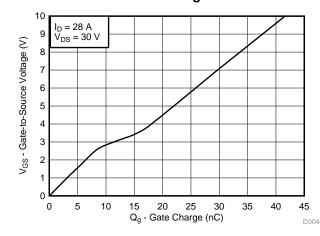




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## 4 Revision History

Changes from Revision A (June 2016) to Revision B						
Corrected package size typo in the <i>Description</i> section						
Changes from Original (June 2014) to Revision A	Page					
Updated I <sub>D</sub> values.	1					
Updated P <sub>D</sub> values	1					
Increased maximum temperature to 175°C.	1					
Updated Figure 2	5					
Changed Figure 6 to extend temperature to 175°C.						
Changed Figure 8 to extend temperature to 175°C.	6					
Replotted Figure 10 using 175°C data	6					
Changed Figure 12 to extend temperature to 175°C.	6					
Added Receiving Notification of Documentation Updates and Community Resources to Device ar Support section.	nd Documentation					
Updated the mechanical drawing						

Product Folder Links: CSD18540Q5B

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## 5 Specifications

#### 5.1 Electrical Characteristics

 $T_{\Delta} = 25^{\circ}C$  (unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS		<u>'</u>		<u> </u>	
BV <sub>DSS</sub>	Drain-to-source voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
I <sub>DSS</sub>	Drain-to-source leakage current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 48 V			1	μА
I <sub>GSS</sub>	Gate-to-source leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I = 250 μA	1.5	1.9	2.3	V
Б	Drain to course an registeres	$V_{GS} = 4.5 \text{ V}, I_D = 28 \text{ A}$		2.6	3.3	mΩ
R <sub>DS(on)</sub>	Drain-to-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 28 \text{ A}$		1.8	2.2	11122
g <sub>fs</sub>	Transconductance	$V_{DS} = 6 \text{ V}, I_{D} = 28 \text{ A}$		116		S
DYNAMI	C CHARACTERISTICS				•	
C <sub>iss</sub>	Input capacitance		3	3250	4230	pF
C <sub>oss</sub>	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		622	808	pF
C <sub>rss</sub>	Reverse transfer capacitance			15	20	pF
$R_{G}$	Series gate resistance			8.0	1.6	Ω
Qg	Gate charge total (4.5 V)			20	26	nC
Qg	Gate charge total (10 V)			41	53	nC
$Q_{gd}$	Gate charge gate-to-drain	V <sub>DS</sub> = 30 V, I <sub>DD</sub> = 28 A		6.7		nC
Q <sub>gs</sub>	Gate charge gate-to-source			8.8		nC
Q <sub>g(th)</sub>	Gate charge at V <sub>th</sub>			6.3		nC
Q <sub>oss</sub>	Output charge	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$		83		nC
t <sub>d(on)</sub>	Turnon delay time			6		ns
t <sub>r</sub>	Rise time	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V},$		9		ns
t <sub>d(off)</sub>	Turnoff delay time	$I_{DS} = 28 \text{ A}, R_G = 0 \Omega$		20		ns
t <sub>f</sub>	Fall time			3		ns
DIODE C	CHARACTERISTICS					-
V <sub>SD</sub>	Diode forward voltage	I <sub>SD</sub> = 28 A, V <sub>GS</sub> = 0 V		8.0	1	V
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DS</sub> = 30 V, I <sub>F</sub> = 28 A,		145		nC
t <sub>rr</sub>	Reverse recovery time	di/dt = 300 A/μs		82		ns

## 5.2 Thermal Information

 $T_A = 25$ °C (unless otherwise stated)

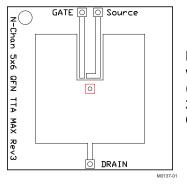
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance <sup>(1)</sup>			8.0	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)(2)</sup>			50	*C/vv

R<sub>θJC</sub> is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-in (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.

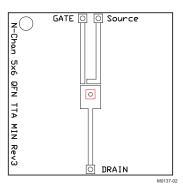
(2) Device mounted on FR4 material with 1-in<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz (0.071-mm) thick Cu.

Product Folder Links: CSD18540Q5B





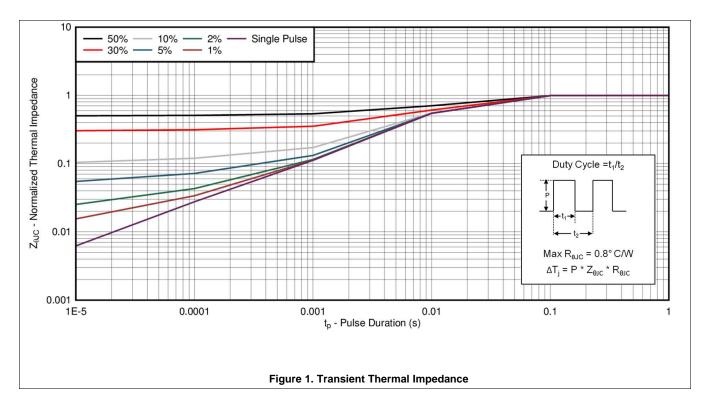
Max  $R_{\theta JA} = 50^{\circ} C/W$  when mounted on 1 in<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-oz (0.071-mm) thick Cu.



Max  $R_{\theta JA} = 125^{\circ}\text{C/W}$  when mounted on a minimum pad area of 2-oz (0.071-mm) thick Cu.

## 5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise stated)

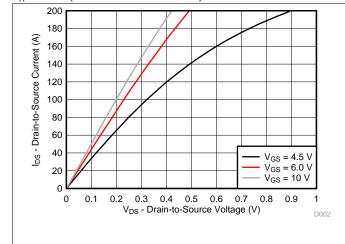


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## **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C (unless otherwise stated)



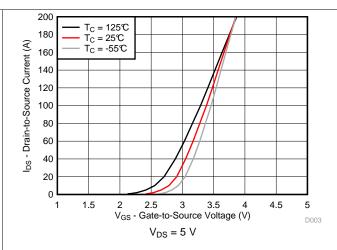
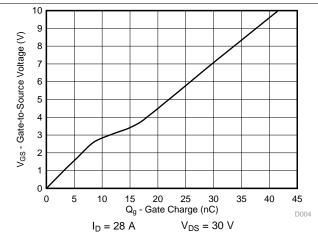


Figure 2. Saturation Characteristics





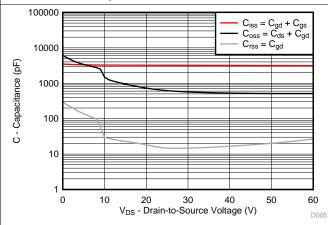
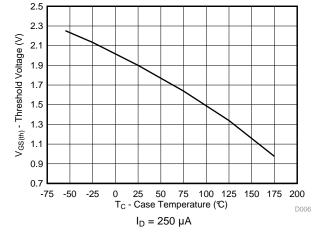


Figure 4. Gate Charge

arge Figure 5. Capacitance



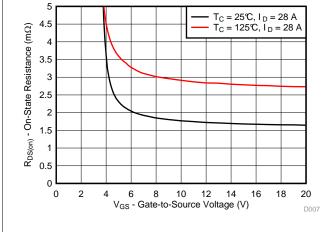


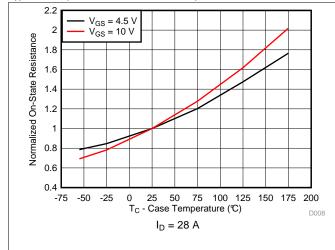
Figure 6. Threshold Voltage vs Temperature

Figure 7. On-State Resistance vs Gate-to-Source Voltage



## **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C (unless otherwise stated)



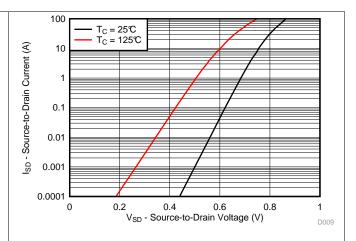


Figure 8. Normalized On-State Resistance vs Temperature

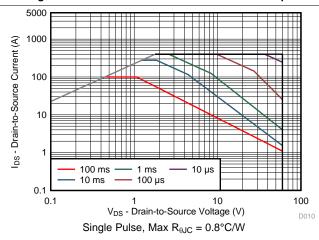


Figure 9. Typical Diode Forward Voltage

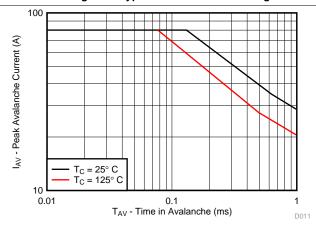


Figure 10. Maximum Safe Operating Area



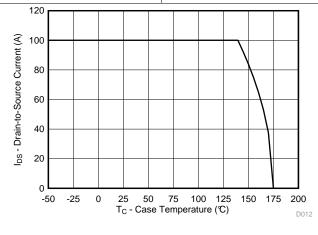


Figure 12. Maximum Drain Current vs Temperature

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## 6 Device and Documentation Support

#### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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#### 6.3 Trademarks

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#### 6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 6.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

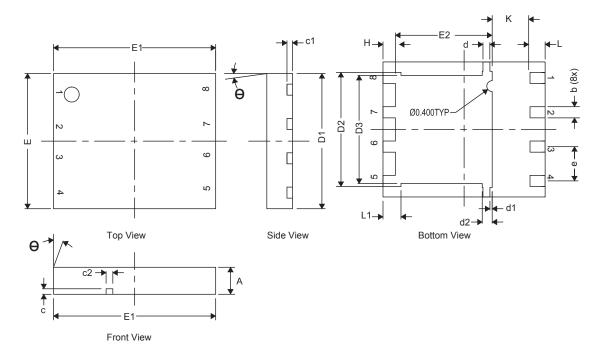
Product Folder Links: CSD18540Q5B



## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## 7.1 Q5B Package Dimensions

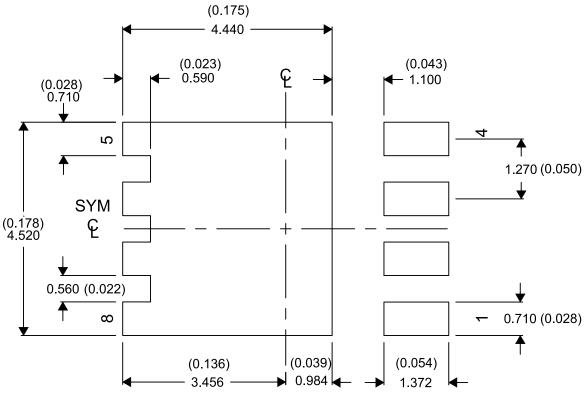


DIM	MILLIMETERS								
DIW	MIN	NOM	MAX						
Α	0.80	1.00	1.05						
b	0.36	0.41	0.46						
С	0.15	0.20	0.25						
c1	0.15	0.20	0.25						
c2	0.20	0.25	0.30						
D1	4.90	5.00	5.10						
D2	4.12	4.22	4.32						
D3	3.90	4.00	4.10						
d	0.20	0.25	0.30						
d1	0.085 TYP								
d2	0.319	0.369	0.419						
E	4.90	5.00	5.10						
E1	5.90	6.00	6.10						
E2	3.48	3.58	3.68						
е		1.27 TYP							
Н	0.36	0.46	0.56						
L	0.46	0.56	0.66						
L1	0.57	0.67	0.77						
θ	0°	<u> </u>							
K		1.40 TYP							

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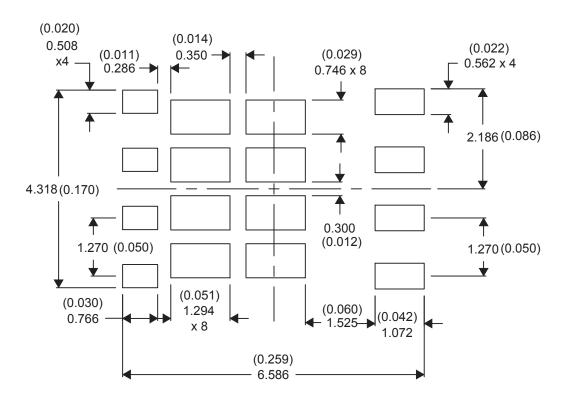


#### 7.2 Recommended PCB Pattern



For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

## 7.3 Recommended Stencil Pattern

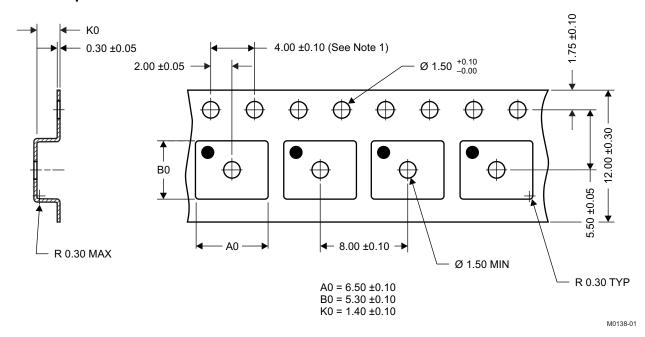


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## 7.4 Q5B Tape and Reel Information



#### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2.
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
- 3. Material: black static-dissipative polystyrene.
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

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## PACKAGE OPTION ADDENDUM

19-Apr-2017

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD18540Q5B	ACTIVE	VSON-CLIP	DNK	8	2500	Pb-Free (RoHS Exempt)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18540	Samples
CSD18540Q5BT	ACTIVE	VSON-CLIP	DNK	8	250	Pb-Free (RoHS Exempt)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18540	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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## **PACKAGE OPTION ADDENDUM**

19-Apr-2017

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